

# 30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

#### **Product Summary**

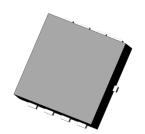
BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C		
001/	12mΩ @ V <sub>GS</sub> = -10V	-35A		
-30V	$21m\Omega$ @ $V_{GS} = -4.5V$	-25A		

## **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# **Applications**

- Backlighting
- Power Management Functions
- DC-DC Converters



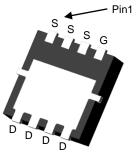
Top View

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub> ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

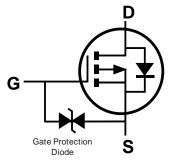
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)



**Bottom View** 





**Equivalent Circuit** 

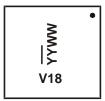
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP3018SFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMP3018SFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



V18 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)

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# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-11 -9	Α
Continuous Drain Current (Note 7) V <sub>GS</sub> = -10V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	-35 -25	Α
Maximum Continuous Body Diode Forward Current (Note 7)			Is	-30	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-70	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-70	Α
Avalanche Current (Note 8) L = 1mH			IAS	-14	Α
Avalanche Energy (Note 8) L = 1mH			E <sub>AS</sub>	104	mJ

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	$P_{D}$	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	133	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	66	°C/W
Total Power Dissipation (Note 7)	PD	30	W	
Thermal Resistance, Junction to Case (Note 7)	Rejc	3.7	°C/W	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

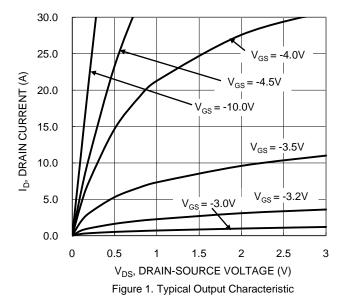
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)						root containen	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	V <sub>DS</sub> = -24V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	•						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		_	_	12	mΩ	$V_{GS} = -10V, I_D = -11.5A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	21	11122	$V_{GS} = -4.5V, I_D = -8.5A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	2,147	_	pF	45)/ )/ 0)/	
Output Capacitance	Coss	_	407	_	pF	$V_{DS} = -15V, V_{GS} = 0V,$	
Reverse Transfer Capacitance	Crss	_	358	_	pF	f = 1.0MHz	
Gate Resistance	Rg	_	24	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = -5V)	Qg	_	28	_	nC		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	51	_	nC	15)/ 14.50	
Gate-Source Charge	Qgs	_	6.6	_	nC	$V_{DS} = -15V, I_{D} = -11.5A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	15	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.8	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	19.9	_	ns	$V_{DD} = -15V$ , $V_{GS} = -10V$ , $R_G = 6\Omega$ , $I_D = -11.5A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	57.5	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	42.8	_	ns		
Reverse Recovery Time	t <sub>RR</sub>	_	21.5	_	ns	1 44.50 41/44 4000/5-	
Reverse Recovery Charge	Q <sub>RR</sub>	_	11.6	_	nC	I <sub>S</sub> = -11.5A, dl/dt = 100A/μs	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.







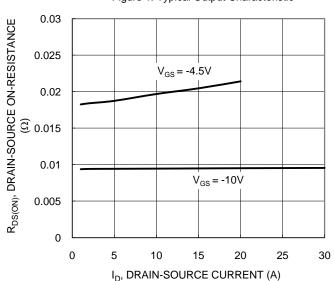
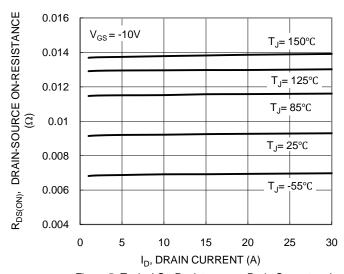


Figure 3. Typical On-Resistance vs. Drain Current and

Gate Voltage





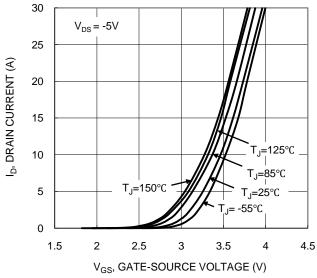


Figure 2.Typical Transfer Characteristic

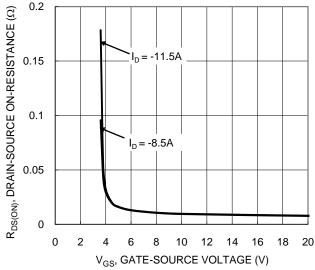


Figure 4. Typical Transfer Characteristic

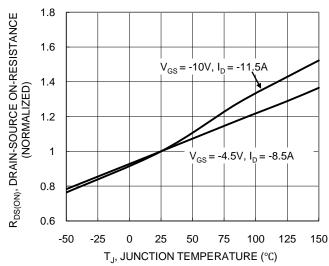


Figure 6. On-Resistance Variation with Junction Temperature



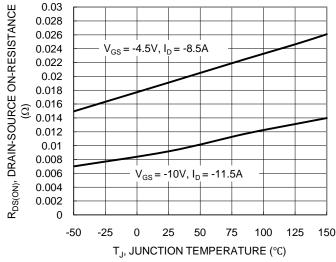
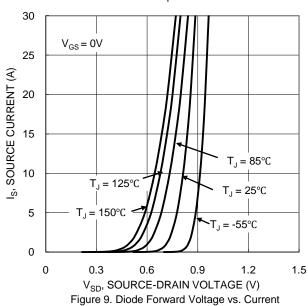
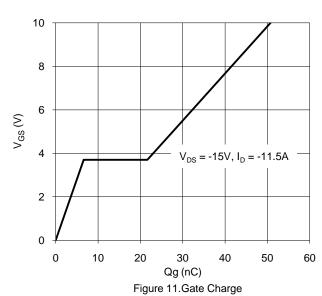


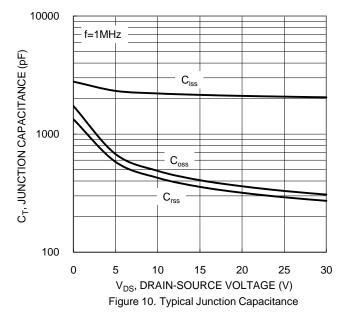
Figure 7. On-Resistance Variation with Junction Temperature

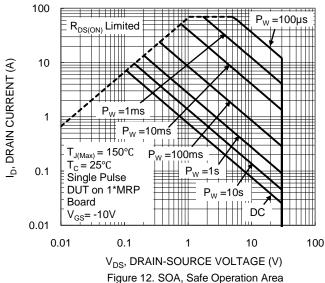




3  $V_{\text{GS}(\text{TH})}$ , GATE THRESHOLD VOLTAGE (V) 2.8 2.6  $I_D = -1mA$ 2.4 2.2  $I_{D} = -250 \mu A$ 2 1.8 1.6 1.4 1.2 1 -50 -25 0 25 50 75 100 125 150 T<sub>.I</sub>, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature







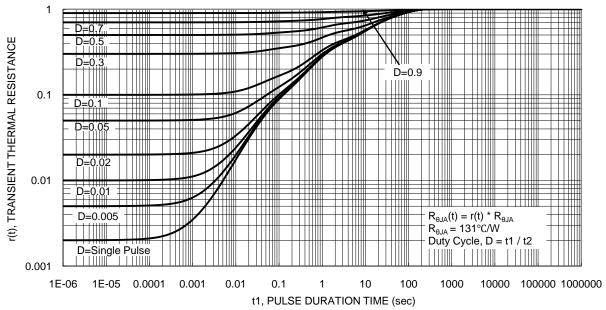


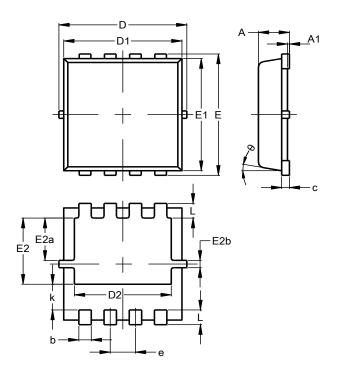
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8 (Type UX)

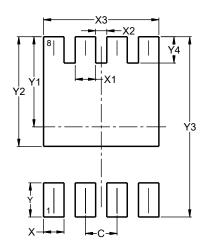


PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур		
A	0.75	0.85	0.80		
A1			0.60		
	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		

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